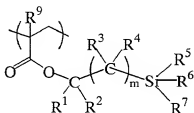
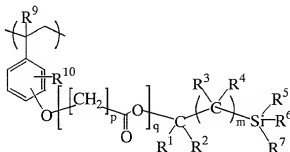




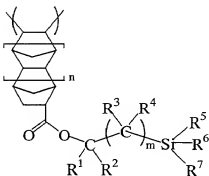
3. A polymer comprising recurring units of one of the general formulae (2) to (5):



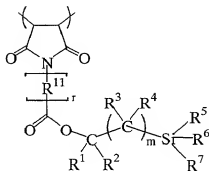
(2)



(3)



(4)



(5)

wherein  $R^1$  to  $R^4$  each are independently hydrogen or a straight, branched or cyclic alkyl group of 1 to 20 carbon atoms, or  $R^1$  and  $R^2$ , taken together, may form an aliphatic hydrocarbon ring in which  $-CH_2-$  may be substituted with a  $-Si(R^8)_2-$  group, and  $R^3$  and  $R^4$ , taken together, may form an aliphatic hydrocarbon ring in which  $-CH_2-$  may be substituted with a  $-Si(R^8)_2-$  group,

$R^5$  to  $R^7$  each are independently a straight, branched or cyclic alkyl or fluorinated alkyl group of 1 to 20 carbon atoms or aryl group of 6 to 20 carbon atoms,

$R^8$  is independently a straight or branched alkyl group of 1 to 4 carbon atoms,

$R^9$  is hydrogen, a straight, branched or cyclic alkyl group of 1 to 20 carbon atoms, or  $CH_3CO_2R^{12}$ ,

$R^{10}$  is hydrogen or a straight, branched or cyclic alkyl group of 1 to 20 carbon atoms,

R<sup>11</sup> is a straight, branched or cyclic alkylene group of 1 to 10 carbon atoms,

R<sup>12</sup> is hydrogen or a straight, branched or cyclic alkyl group of 1 to 20 carbon atoms,

5 m is 1 or 2, n is a number of 0 to 5, p is a number of 1 to 5, each of q and r is 0 or 1.

4. A chemically amplified positive resist composition comprising:

- 10 (A) the polymer of claim 1,  
(B) a photoacid generator, and  
(C) an organic solvent.

15 5. The resist composition of claim 4 further comprising a basic compound.

6. A chemically amplified positive resist composition comprising:

- 20 (A) the polymer of claim 1,  
(B) a photoacid generator,  
(C) an organic solvent, and  
(D) a dissolution rate inhibitor having an acid labile group.

25 7. The resist composition of claim 6 further comprising a basic compound.

8. A process for forming a pattern, comprising the steps of:

- 30 applying the positive resist composition of claim 4 onto an organic film on a substrate to form a coating,  
prebaking the coating to form a resist film,  
exposing the resist film in a pattern circuit region to radiation,  
35 post-exposure baking the resist film,

developing the resist film with an aqueous alkaline solution to dissolve away the exposed area, thereby forming a resist pattern, and

5 processing the organic film with an oxygen plasma generated by a dry etching apparatus.